10 649050

IN UNITED STATES PATENT AND TRADEMARK OFFICE

Pater No.: 7,338,856

ue Date: March 4, 2008

Docket No: 2000-0879.01/US

CUFC

Patentee: Chun Chen et al.

Title: DOUBLE-DOPED POLYSILICON FLOATING GATE

REQUEST FOR CERTIFICATION OF CORRECTION

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

ATTN: Certificate of Correction Branch

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. Two copies of the text of the Certificate in the suggested form are enclosed.

Pursuant to 1.20(a), the examiner is authorized to charge the Certificate of Correction fee of \$100.00 to the Deposit Account No. 13-3092.

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims as properly allowed, and re-examination is not required.

Respectfully submitted,

Customer Number: 26809

Date: March 13, 2008

Russ Slifer

Reg. No. 39,838

<u>CERTIFICATE UNDER 37 CFR § 1.8:</u> The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450, on this 13th day of <u>March</u> 2008

Christine Hartness

Name

Signature

Christine Hartness

03/18/2008 EEKUBAY1 00000007 133092 7338856

01 FC:1811

100.00 DA

RECEIVED-USPTO
Patent Publication

Certificate

MAR 1 9 2008

of Correction

MAR 1 9 2008



Name

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chun Chen et al. Examiner: Chuong A Luu Group Art Unit: 2818 Patent No.: 7,338,856 Docket No: 2000-0879.01/US Issue Date: March 4, 2008 Title: DOUBLE-DOPED POLYSILICON FLOATING GATE Commissioner for Patents Office of Patent Publication ATTN: Certificate of Correction Branch We are transmitting herewith the attached: Authorization to charge the Certificate of Correction fee of \$100.00 to the Deposit Account No. 13-3092. Request for Certificate of Correction. Certificate of Correction Form - PTO-1050 (in duplicate) A return postcard. Please charge any additional fees or credit overpayment to Deposit Account No. 13-3092. Customer Number: 26809 Respectfully submitted, Date: March 13, 2008 By: Russ Slifer Reg. No. 39,838 CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents and Trademarks, P.O. Box 1450, Alexandria VA 22313-1450, on this 13th day of March 2008. Christine Hartness Christine Hartness

Signature

PTO/SB/44 (02-01) PTO/SB/44 (02-01) Approved for use through 01/31/2004. OMB 0651-0033 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. (Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO

: 7,338,856

Page (1) of 1

DATED

: March 4, 2008

INVENTOR(S)

: Chen et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 10, lines 56–58, in Claim 8, delete "introducing dopant atoms of the first type of dopant material into the first polysilicon layer" and insert - - forming the first polysilicon layer - -, therefor.

Approved for use through 01/31/2004. OMB 0651-0033

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO

: 7,338,856

Page (1) of 1

DATED

: March 4, 2008

INVENTOR(S)

: Chen et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 10, lines 56–58, in Claim 8, delete "introducing dopant atoms of the first type of dopant material into the first polysilicon layer" and insert - - forming the first polysilicon layer - -, therefor.